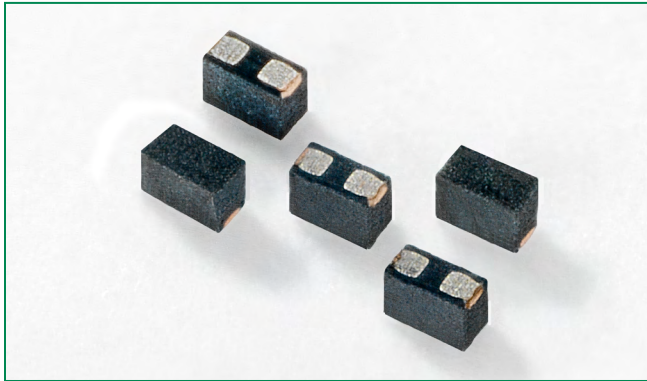


SP1006 Series 25pF 30kV Unidirectional Discrete TVS



Pinout



Functional Block Diagram



Additional Information



Description

Zener diodes fabricated in a proprietary silicon avalanche technology protect each I/O pin to provide a high level of protection for electronic equipment that may experience destructive electrostatic discharges (ESD). These robust diodes can safely absorb repetitive ESD strikes at $\pm 30\text{kV}$ (contact discharge, IEC 61000-4-2) without performance degradation. Additionally, each diode can safely dissipate 5A of 8/20 μs surge current (IEC61000-4-5) with very low clamping voltages.

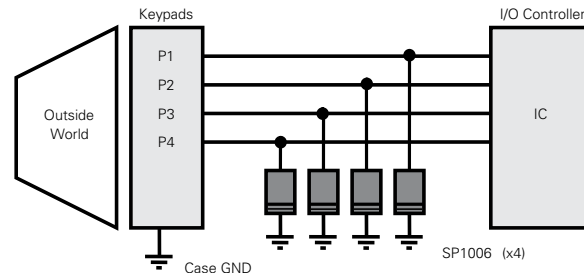
Features

- ESD, IEC61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC61000-4-4, 40A (5/50ns)
- Lightning, IEC61000-4-5, 5A (8/20 μs)
- Low leakage current of 0.5 μA (MAX) at 5V
- Space efficient 0201 footprint)

Applications

- Mobile phones
- Smart phones
- PDAs
- Digital cameras
- Portable navigation devices
- Portable medical devices

Application Example



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Absolute Maximum Ratings

| Symbol | Parameter | Value | Units |
|------------|--|------------|-------|
| I_{PP} | Peak Pulse Current ($t_p=8/20\mu s$) | 5 | A |
| T_{OP} | Operating Temperature | -40 to 125 | °C |
| T_{STOR} | Storage Temperature | -55 to 150 | °C |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Thermal Information

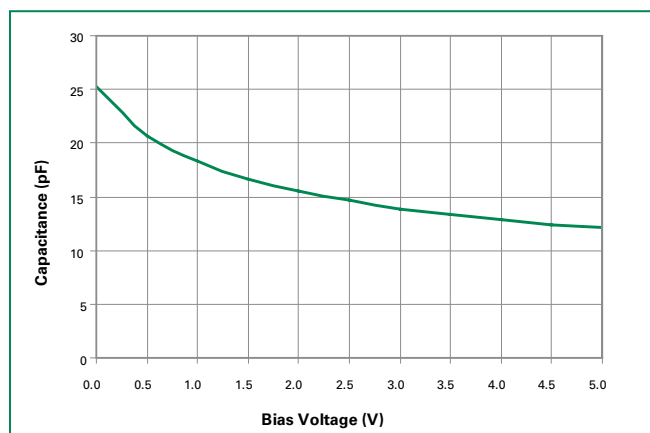
| Parameter | Rating | Units |
|--|------------|-------|
| Storage Temperature Range | -55 to 150 | °C |
| Maximum Junction Temperature | 150 | °C |
| Maximum Lead Temperature (Soldering 30s) | 260 | °C |

Electrical Characteristics ($T_{OP}=25^\circ C$)

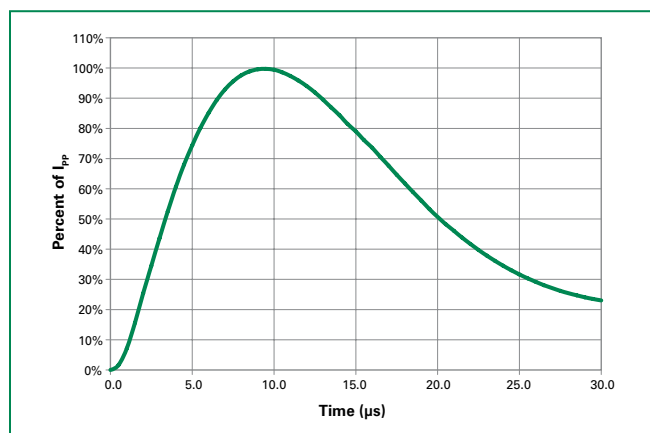
| Parameter | Symbol | Test Conditions | Min | Typ | Max | Units |
|------------------------------------|------------|---|----------|-----|-----|----------|
| Reverse Standoff Voltage | V_{RWM} | | | | 6.0 | V |
| Breakdown Voltage | V_{BR} | $I_R=1mA$ (Pin 1 to 2) | | 7.8 | | V |
| Forward Voltage Drop | V_F | $I_R=1mA$ (Pin 2 to 1) | | 0.8 | | V |
| Leakage Current | I_{LEAK} | $V_R=5V$ | | 0.1 | 0.5 | μA |
| Clamp Voltage ¹ | V_C | $I_{PP}=1A, t_p=8/20\mu s$ (Pin 1 to 2) | | 8.3 | | V |
| | | $I_{PP}=2A, t_p=8/20\mu s$ (Pin 1 to 2) | | 9.2 | | V |
| Dynamic Resistance | R_{DYN} | $(V_{C2} - V_{C1}) / (I_{PP2} - I_{PP1})$ | | 0.9 | | Ω |
| ESD Withstand Voltage ¹ | V_{ESD} | IEC61000-4-2 (Contact Discharge) | ± 30 | | | kV |
| | | IEC61000-4-2 (Air Discharge) | ± 30 | | | kV |
| Diode Capacitance ¹ | C_D | Reverse Bias=0V | | 25 | | pF |
| | | Reverse Bias=2.5V | | 15 | | pF |

Note: ¹ Parameter is guaranteed by design and/or device characterization.

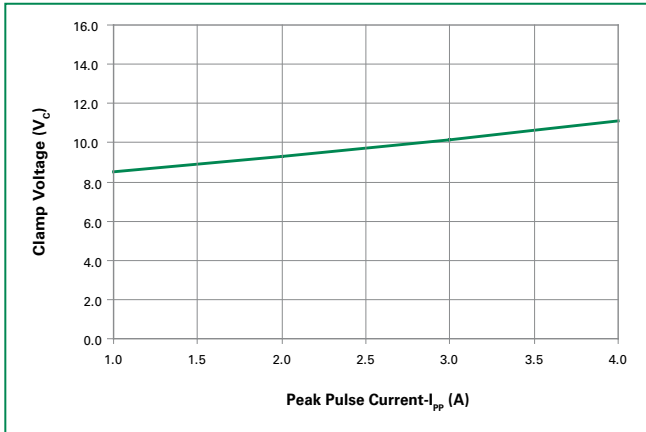
Capacitance vs. Reverse Bias



Pulse Waveform

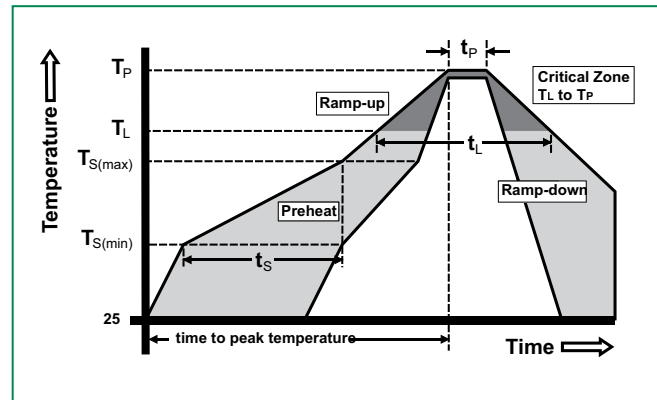


Clamping Voltage vs. I_{pp}

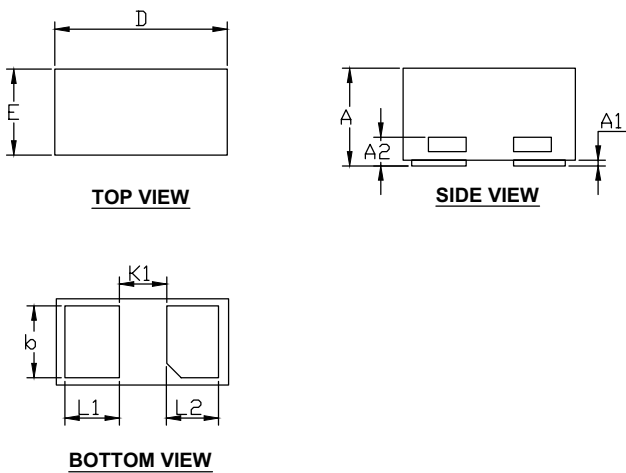


Soldering Parameters

| | | |
|--|------------------------------------|-------------------------|
| Reflow Condition | | Pb – Free assembly |
| Pre Heat | - Temperature Min ($T_{s(min)}$) | 150°C |
| | - Temperature Max ($T_{s(max)}$) | 200°C |
| | - Time (min to max) (t_s) | 60 – 180 secs |
| Average ramp up rate (Liquidus) Temp (T_L) to peak | | 3°C/second max |
| $T_{s(max)}$ to T_L - Ramp-up Rate | | 3°C/second max |
| Reflow | - Temperature (T_L) (Liquidus) | 217°C |
| | - Temperature (t_L) | 60 – 150 seconds |
| Peak Temperature (T_p) | | 260 ^{+0/-5} °C |
| Time within 5°C of actual peak Temperature (t_p) | | 20 – 40 seconds |
| Ramp-down Rate | | 6°C/second max |
| Time 25°C to peak Temperature (T_p) | | 8 minutes Max. |

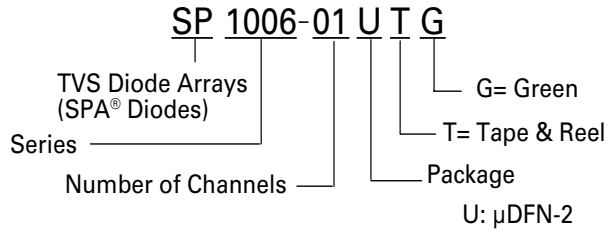


Package Dimensions – μ DFN-2 (0201)



| Package | μ DFN-2 (0201) | | |
|-----------|--------------------|------|------|
| JEDEC | MO-236 | | |
| Symbol | Millimeters | | |
| | Min | Nom | Max |
| A | 0.28 | 0.30 | 0.32 |
| A1 | 0.00 | 0.02 | 0.05 |
| A2 | 0.05 | 0.10 | 0.15 |
| b | 0.20 | 0.25 | 0.30 |
| D | 0.55 | 0.60 | 0.65 |
| E | 0.25 | 0.30 | 0.35 |
| L1 | 0.14 | 0.19 | 0.24 |
| L2 | 0.13 | 0.18 | 0.23 |
| K1 | 0.165 REF | | |

Part Numbering System



Part Marking System



Ordering Information

| Part Number | Package | Marking | Min. Order Qty. |
|--------------|-------------|---------|-----------------|
| SP1006-01UTG | μ DFN-2 | | 10000 |

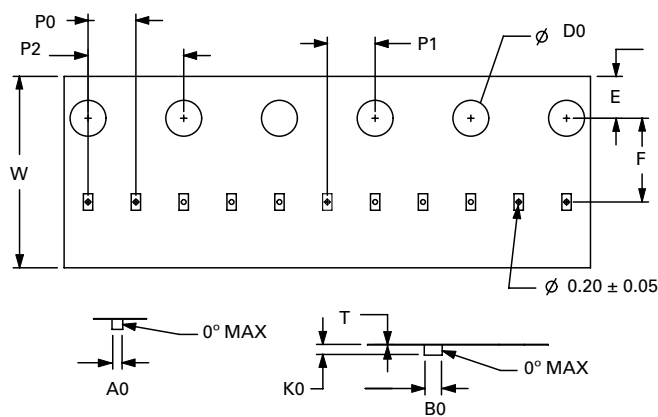
Product Characteristics

| | |
|----------------------------|-------------------------|
| Lead Plating | Pre-Plated Frame |
| Lead Material | Copper Alloy |
| Lead Coplanarity | 0.0004 inches (0.102mm) |
| Substitute Material | Silicon |
| Body Material | Molded Epoxy |
| Flammability | UL 94 V-0 |

Notes :

1. All dimensions are in millimeters
2. Dimensions include solder plating.
3. Dimensions are exclusive of mold flash & metal burr.
4. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
5. Package surface matte finish VDI 11-13.

Embossed Carrier Tape & Reel Specification – μ DFN-2



| Symbol | Millimetres | | Inches | |
|-----------|-------------|------|--------|-------|
| | Min | Max | Min | Max |
| A0 | 0.36 | 0.42 | 0.014 | 0.017 |
| B0 | 0.66 | 0.72 | 0.026 | 0.028 |
| D0 | 1.40 | 1.60 | 0.055 | 0.063 |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 3.45 | 3.55 | 0.136 | 0.140 |
| K0 | 0.39 | 0.45 | 0.015 | 0.018 |
| P0 | 1.95 | 2.05 | 0.077 | 0.081 |
| P1 | 1.95 | 2.05 | 0.077 | 0.081 |
| P2 | 3.90 | 4.10 | 0.154 | 0.161 |
| T | 0.18 | 0.22 | 0.007 | 0.009 |
| W | 7.90 | 8.30 | 0.311 | 0.327 |